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# **DATASHEET**

# 6 PIN DIP PHOTOTRANSISTOR PHOTOCOUPLER 4N2X Series 4N3X Series H11AX Series



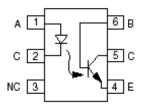




### Features:

- 4N2X series: 4N25, 4N26, 4N27, 4N28
- 4N3X series: 4N35, 4N36, 4N37, 4N38
- H11AX series: H11A1, H11A2, H11A3, H11A4, H11A5
- High isolation voltage between input and output (Viso=5000 V rms)
- Creepage distance >7.62 mm
- Operating temperature up to +110°C
- · Compact dual-in-line package
- Pb free and RoHS compliant.
- UL approved (No. E214129)
- VDE approved (No. 132249)
- SEMKO approved
- NEMKO approval
- DEMKO approval
- FIMKO approval
- CSA approved
- CQC approved

### Schematic



### Pin Configuration

- 1. Anode
- 2. Cathode
- 3. No Connection
- 4. Emitter
- 5. Collector
- 6. Base

## **Description**

The 4N2X, 4N3X, H11AX series of devices each consist of an infrared emitting diode optically coupled to a phototransistor.

They are packaged in a 6-pin DIP package and available in wide-lead spacing and SMD option.

# **Applications**

- Power supply regulators
- Digital logic inputs
- Microprocessor inputs



# Absolute Maximum Ratings (Ta=25℃)

	Parameter	Symbol	Rating	Unit
	Forward current	I <sub>F</sub>	60	mA
	Peak forward current (t = 10µs)	I <sub>FM</sub>	1	А
Input	Reverse voltage	$V_{R}$	6	V
	Power dissipation (T <sub>A</sub> = 25°C)	P <sub>D</sub> —	100	mW
	Derating factor (above 100°C)	r <sub>D</sub> —	3.8	mW/°C
	Collector-Emitter voltage	$V_{CEO}$	80	V
	Collector-Base voltage	$V_{CBO}$	80	V
Output	Emitter-Collector voltage	V <sub>ECO</sub>	7	V
	Emitter-Base voltage	$V_{EBO}$	7	V
	Power dissipation (T <sub>A</sub> = 25°C)	D	150	mW
	Derating factor (above 100°C)	P <sub>C</sub> —	9.0	mW/°C
Total Power Dissipation		P <sub>TOT</sub> 200		mW
Isolation Voltage*1		V <sub>ISO</sub>	5000	V rms
Operating Temperature		T <sub>OPR</sub>	T <sub>OPR</sub> -55 to 110	
Storage Temperature		T <sub>STG</sub>	T <sub>STG</sub> -55 to 125	
Soldering Temperature*2		T <sub>SOL</sub>	260	°C

### Notes:

<sup>\*1</sup> AC for 1 minute, R.H.= 40 ~ 60% R.H. In this test, pins 1, 2 & 3 are shorted together, and pins 4, 5 & 6 are shorted together.

<sup>\*2</sup> For 10 seconds



# Electro-Optical Characteristics (Ta=25℃ unless specified otherwise)

Input

Parameter	Symbol	Min.	Тур.	Max.	Unit	Condition
Forward voltage	$V_{F}$	-	1.2	1.5	V	I <sub>F</sub> = 10mA
Reverse current	I <sub>R</sub>	-	-	10	μΑ	$V_R = 6V$
Input capacitance	C <sub>in</sub>	-	30	-	pF	V = 0, f = 1MHz

Output

Parameter		Symbol	Min	Тур.	Max.	Unit	Condition
Collector-Base dark current		$I_{CBO}$	-	-	20	nA	V <sub>CB</sub> = 10V
Collector- Emitter dark current	4N2X H11AX	- loso -	-	-	50	- nA	V <sub>CE</sub> = 10V, IF=0mA
	4N3X	- ICEO	-	-	50		V <sub>CE</sub> = 60V, IF=0mA
Collector-Emitter breakdown voltage		$BV_CEO$	80	-	-	V	I <sub>c</sub> =1mA
Collector-Base breakdown voltage		BV <sub>CBO</sub>	80	-	-	٧	I <sub>C</sub> =0.1mA
Emitter-Collector breakdown voltage		$BV_{ECO}$	7	-	-	٧	I <sub>E</sub> =0.1mA
Emitter-Base breakdown voltage		$BV_{EBO}$	7	-	-	٧	I <sub>E</sub> =0.1mA
Collector-Emitter capacitance		$C_CE$	-	8	-	pF	VCE=0V, f=1MHz

<sup>\*</sup> Typical values at T<sub>a</sub> = 25°C



# **Transfer Characteristics**

Parameter		Symbol	Min	Тур.	Max.	Unit	Condition	
Current Transfer ratio	4N35, 4N36, 4N37	CTR .	100	-	-			
	H11A1		50	-	-	- %		
	H11A5		30	-	-		$I_F = \pm 10 \text{mA} , V_{CE} = 10 \text{V}$	
	4N25, 4N26, 4N38, H11A2, H11A3		20	-	-			
	4N27, 4N28, H11A4		10	-	-			
	4N25, 4N26, 4N27, 4N28		-	-	0.5	V	$I_F = 50 \text{mA}, I_C = 2 \text{mA}$	
Collector- Emitter	4N35, 4N36, 4N37	V <sub>CE(sat)</sub>	-	-	0.3			
saturation voltage	H11A1,H11A2, H11A3,H11A4, H11A5		-	-	0.4		$I_F = 10 \text{mA}, I_c = 0.5 \text{mA}$	
	4N38		-	-	1.0		$I_F = 20$ mA, $I_c = 4$ mA	
Isolation resistance		R <sub>IO</sub>	10 <sup>11</sup>	-	-	Ω	V <sub>IO</sub> = 500Vdc	
Input-output	Input-output capacitance		-	0.2	-	pF	$V_{IO} = 0$ , $f = 1MHz$	
Turn-on time	4N25, 4N26, 4N27, 4N28, H11A1,H11A2, H11A3,H11A4, H11A5	Ton	-	3	10	μs ·	$V_{CC}$ = 10V, $I_F$ = 10mA, $R_L$ = 100 $\Omega$ See Fig. 11	
	4N35, 4N36, 4N37, 4N38		-	10	12		$V_{CC}$ = 10V, $I_C$ = 2mA, $R_L$ = 100 $\Omega$ , See Fig. 11	
Turn-off time	4N25, 4N26, 4N27, 4N28, H11A1,H11A2, H11A3,H11A4, H11A5	Toff	-	3	10	μs	$V_{CC}$ = 10V, $I_F$ = 10mA, $R_L$ = 100 $\Omega$ See Fig. 11	
	4N35, 4N36, 4N37, 4N38		-	9	12		$V_{CC}$ = 10V, $I_C$ = 2mA, $R_L$ = 100 $\Omega$ , See Fig. 11	

<sup>\*</sup> Typical values at  $T_a = 25$ °C



## **Typical Electro-Optical Characteristics Curves**

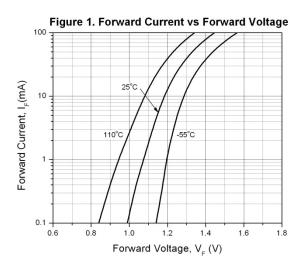


Figure 2. Current Tranfer Ratio vs Forward Current

1.2

0.8

0.8

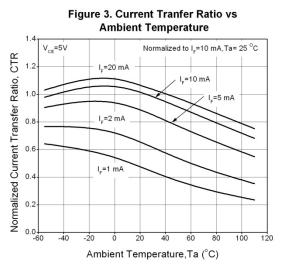
0.4

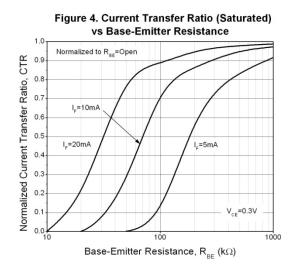
V<sub>cE</sub>=5 V

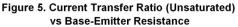
Ta=25°C

Normalized to I<sub>p</sub>=10 mA

Forward Current, I<sub>F</sub> (mA)







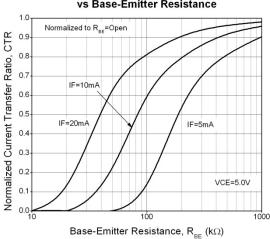
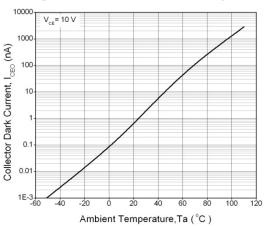


Figure 6. Dark Current vs Ambient Temperature



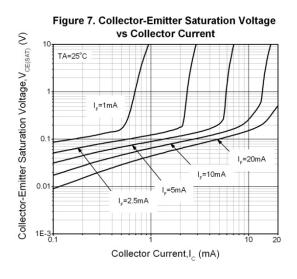
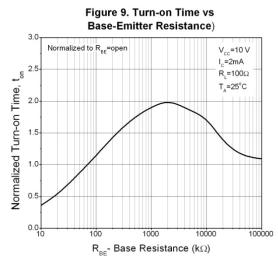
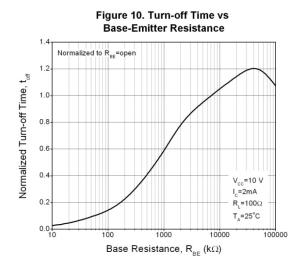
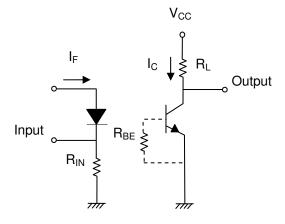


Figure 8. Switching Time vs Load Resistance  $V_{co} = 10 \text{ V}$ Load resistance,  $V_{co} = 10 \text{ V}$ Load resistance,  $V_{co} = 10 \text{ V}$ 







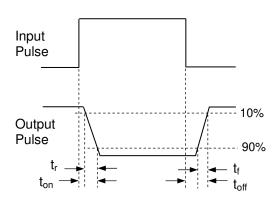


Figure 11. Switching Time Test Circuit & Waveforms



### **Order Information**

**Part Number** 

4NXXY(Z)-V or H11AXY(Z)-V

### Note

XX = Part no. for 4NXX series (25, 26, 27, 28, 35, 36, 37 or 38)

X = Part no. for H11AX series (1, 2, 3, 4, or 5)

Y = Lead form option (S, S1, M or none)

Z = Tape and reel option (TA, TB or none).

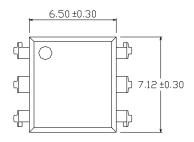
V = VDE safety (optional)

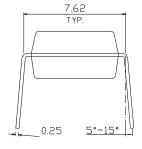
Option	Description	Packing quantity
None	Standard DIP-6	65 units per tube
М	Wide lead bend (0.4 inch spacing)	65 units per tube
S (TA)	Surface mount lead form + TA tape & reel option	1000 units per reel
S (TB)	Surface mount lead form + TB tape & reel option	1000 units per reel
S1 (TA)	Surface mount lead form (low profile) + TA tape & reel option	1000 units per reel
S1 (TB)	Surface mount lead form (low profile) + TB tape & reel option	1000 units per reel

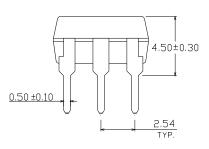


# Package Dimension (Dimensions in mm)

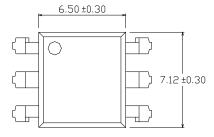
# **Standard DIP Type**

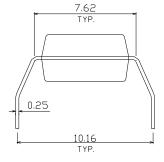


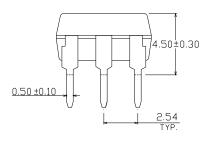




### **Option M Type**

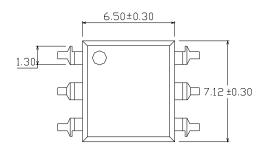


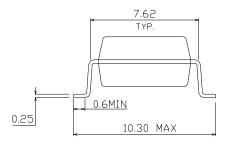


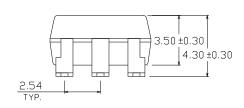




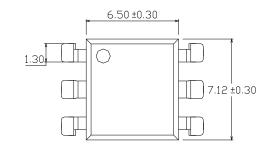
# **Option S Type**

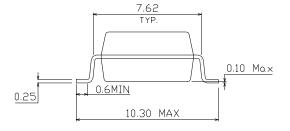


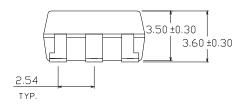




# **Option S1 Type**

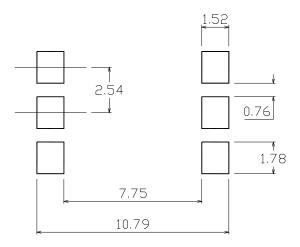




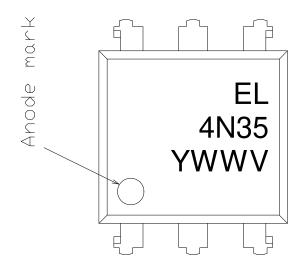




# Recommended pad layout for surface mount leadform



# **Device Marking**



### **Notes**

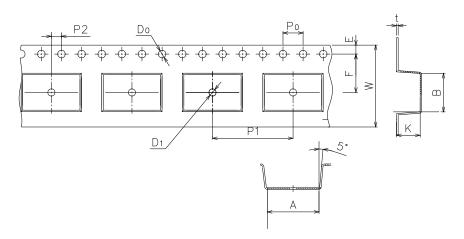
EL denotes Everlight
4N35 denotes Device Number
Y denotes 1 digit Year code
WW denotes 2 digit Week code
V denotes VDE (optional)



**Tape & Reel Packing Specifications** 

# Option TA Option TB Option TB Option TB Option TB Direction of feed from reel

# **Tape dimensions**



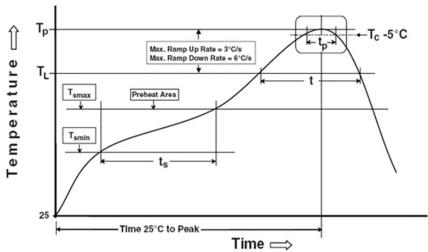
Dimension No.	Α	В	Do	D1	E	F
Dimension (mm)	10.4±0.1	7.5±0.1	1.5±0.1	1.5+0.1/-0	1.75±0.1	7.5±0.1
Dimension No.	Ро	P1	P2	t	W	К
Dimension (mm)	4.0±0.15	12±0.1	2.0±0.1	0.35±0.03	16.0±0.2	4.5±0.1



### **Precautions for Use**

### 1. Soldering Condition

1.1 (A) Maximum Body Case Temperature Profile for evaluation of Reflow Profile



Reference: IPC/JEDEC J-STD-020D Note:

### **Preheat**

150 °C Temperature min (T<sub>smin</sub>) Temperature max (T<sub>smax</sub>) 200°C Time  $(T_{smin} \text{ to } T_{smax})$   $(t_s)$ 60-120 seconds 3 °C/second max

Average ramp-up rate (T<sub>smax</sub> to T<sub>p</sub>)

### Other

Liquidus Temperature (T<sub>L</sub>) 217 °C Time above Liquidus Temperature (t L) 60-100 sec 260°C Peak Temperature (T<sub>P</sub>) Time within 5 °C of Actual Peak Temperature: T<sub>P</sub> - 5°C 30 s

Ramp- Down Rate from Peak Temperature

Time 25°C to peak temperature

Reflow times

6°C /second max.

8 minutes max.

3 times



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